
HRB0103A

Silicon Schottky Barrier Diode
for Low Voltage High Speed Switching , Rectifying

HITACHI

ADE-208-490(Z)
Rev 0

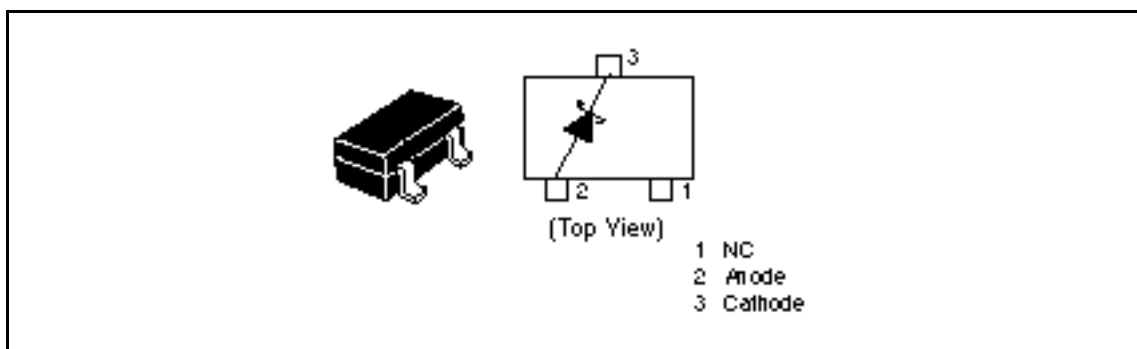
Features

- Σ Low forward voltage drop and suitable for high efficiency forward current.
- Σ CMPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HRB0103A	E1	CMPAK

Outline



HRB0103A

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	30	V
Average rectified current	I_o^{*1}	100	mA
Non-Repetitive peak forward surge current	I_{FSM}^{*2}	3	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. See Fig.5
2. 10msec sine wave 1 pulse

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	0.44	V	$I_F = 100\text{ mA}$
Reverse current	I_R	—	—	50	mA	$V_R = 30\text{V}$

Main Characteristic

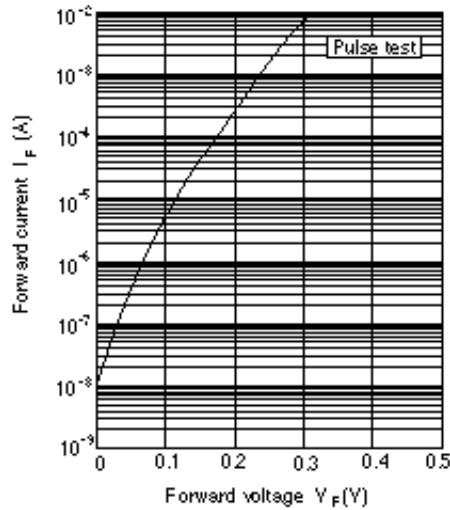


Fig.1 Forward current I_F Vs. Forward voltage

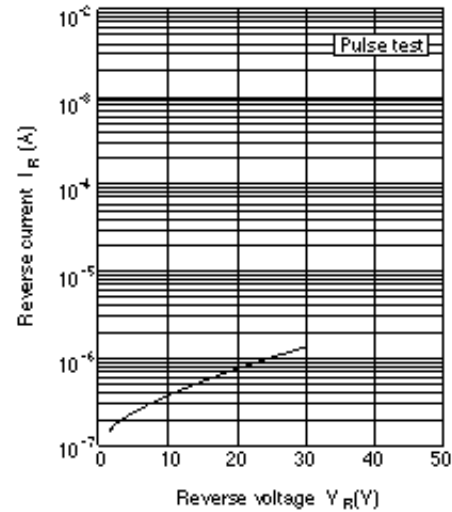


Fig.2 Reverse current I_R Vs. Reverse voltage

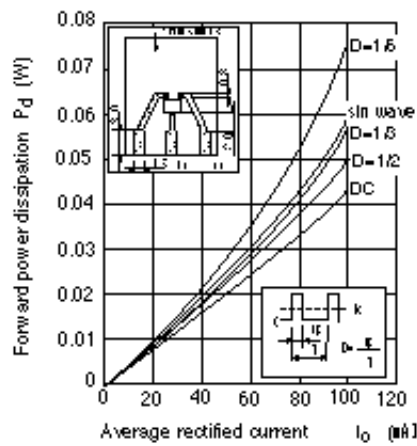


Fig.3. Forward power dissipation P_d Vs. Average rectified current

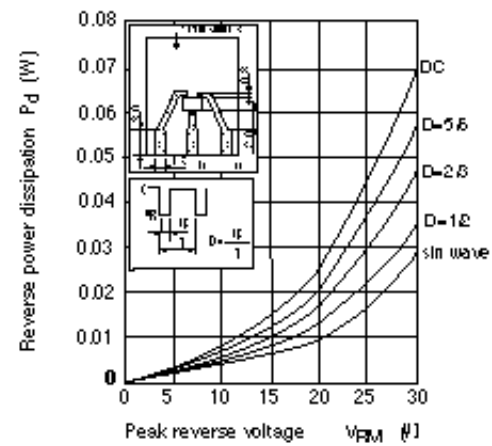


Fig.4. Reverse power dissipation P_d Vs. Peak reverse voltage

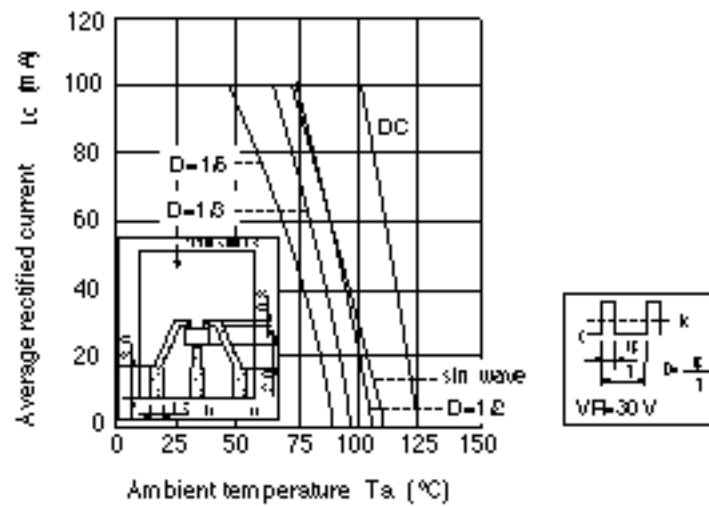
Main Characteristic


Fig.5 Average rectified current Vs. Ambient temperature

Package Dimensions

Unit : mm

